

FMMT416

NPN HIGH VOLTAGE AVALANCHE TRANSISTOR IN SOT23

Features

- 60A Peak Avalanche Current
- $BV_{CBO} > 315V$
- BVcFo > 100V
- Specifically Designed for Avalanche Mode Operation
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

Description

The FMMT416 is a silicon planar bipolar transistor designed for operating in avalanche mode. Tight process control and low inductance packaging combine to produce high-current pulses with fast edges.

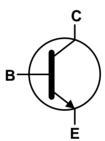
Applications

- Laser Diode Drivers for Ranging and Measurement (LIDAR)
- Radar Systems
- Fast Edge Switch Generator
- **High-Speed Pulse Generators**

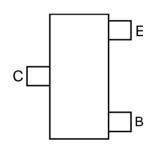








Device Symbol



Top View Pin-Out

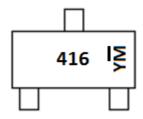
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FMMT416TD	416	7	8	500
FMMT416TA	416	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



416 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	202	3 20	24 2	025	2026	2027	2028	2029
Code	G	Н	I	J	K	l	_	M	N	0	Р	Q
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

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Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	315	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	500	mA
Peak Collector Current (Pulse Width = 20ns)	Ісм	60	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	500	mW
Thermal Resistance, Junction to Ambient	(Note 5)	R _{0JA}	250	°C/W
Thermal Resistance, Junction to Leads	(Note 6)	R _{0JL}	197	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

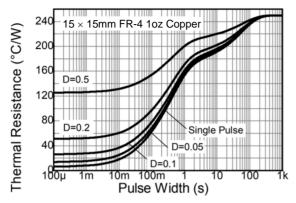
ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

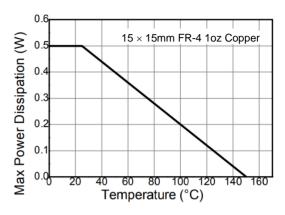
^{5.} For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Thermal resistance from junction to solder-point (at the end of the collector lead).
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



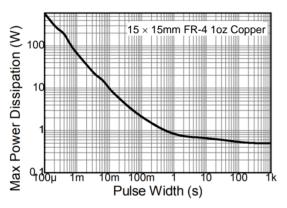
Thermal Characteristics and Derating information



Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	315	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BV _{CEO}	100	_	_	V	$I_C = 100\mu A$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	$I_E = 100 \mu A$
Collector Cutoff Current	I _{CBO}	_	_	100 10	nΑ μΑ	V _{CB} = 310V V _{CB} = 310V, T _J = +100°C
Emitter Cutoff Current	I _{EBO}	-	_	20	nA	V _{EB} = 6V
Static Forward Current Transfer Ratio (Note 8)	h _{FE}	100	_	_	_	$I_C = 10 \text{mA}, V_{CE} = 10 \text{V}$
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	_	_	100	mV	$I_C = 10$ mA, $I_B = 1$ mA
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	1	_	800	mV	$I_C = 10$ mA, $I_B = 1$ mA
Current in Second Breakdown (Pulsed)	l _{USB}		25 35	_	A A	$V_C = 200V, C_{CE} = 620pF$ $V_C = 250V, C_{CE} = 620pF$
Collector-Emitter Inductance	L _{ce}	_	2.5	_	nΗ	Standard SOT23 leads
Output Capacitance	C _{cbo}		_	8	pF	V _{CB} = 20V, I _E = 0 f = 100MHz
Transition Frequency	f⊤	40	_	_	MHz	V _{CE} = 20V, I _C = 10mA, f = 20MHz

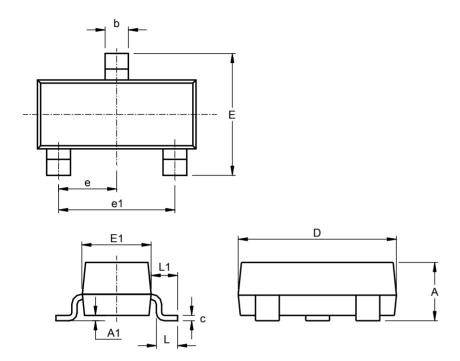
Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)

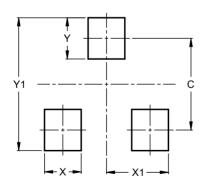


SOT23 Type DN						
Dim	Min	Max	Тур			
Α	0.89	1.12	1.00			
A1	0.01	0.10	0.05			
b	0.30	0.51	0.45			
С	0.08	0.20	0.10			
D	2.80	3.04	3.00			
Е	2.10	2.64	2.42			
E1	1.20	1.40	1.37			
е	0.95 REF					
e1	1.90 REF					
L	0.25	0.60	0.30			
L1	0.45	0.62	0.54			
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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